



SIHU6N62E-GE3 Information



For Reference Only

Part Number SIHU6N62E-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 620V 6A TO-251

Package TO-251-3 Short Leads, IPak, TO-251AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SIHU6N62E-GE3 Specifications

Manufacturer Part Number Manufacturer Vishay Siliconix Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature SIHU6N62E-GE3 Vishay Siliconix Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-251-3 Short Leads, IPak, TO-251AA Series - 10-251-3 Short Leads, IPak, TO-251AA - 10-251-4 All Series - 10-251-4
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Transistors - FETs, MOSFETs - Single Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Tennsistors - FETs, MOSFETs - Single TO-251-3 Short Leads, IPak, TO-251AA Series - TO-251-3 Short Leads, IPak, TO-251AA A VO-251AA Series - To-251-3 Short Leads, IPak, TO-251AA Series - To-251-4 Short Leads, IPak, TO-25
Package TO-251-3 Short Leads, IPak, TO-251AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature TO-251-3 Short Leads, IPak, TO-251AA - 10-251-3 Short Leads, IPak, TO-251AA 10-251AA
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 620V Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 34nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 578pF @ 100V Vgs (Max) ±30V FET Feature -
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Vgs (Max) ±30V FET Feature -
FET Feature -
Power Dissipation (Max) 78W (Tc)
Rds On (Max) @ Id, Vgs 900 mOhm @ 3A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Through Hole
Supplier Device Package IPAK (TO-251)
Package / Case TO-251-3 Short Leads, IPak, TO-251AA
Report errors

SIHU6N62E-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIHU6N62E-GE3 Payment Methods



















SIHU6N62E-GE3 Shipping Methods













If you have any question about SIHU6N62E-GE3, please do not hesitate to contact us!

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